

N-Channel Enhancement Mode Power MOSFET

General Description

The HM10DN06Q is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charges for most of the synchronous buck converter applications.

The HM10DN06Q meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Application

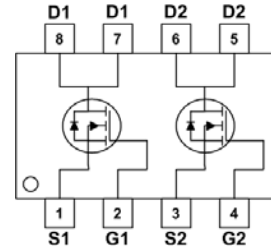
- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

Features

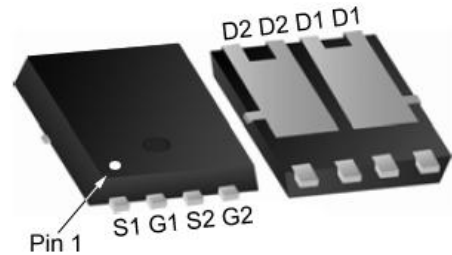
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

BVDSS	RDSON	ID
60V	34 mΩ	10 A



Schematic diagram



PDFN3333-8 top view

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_D@T_C=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
I_{DM}	Pulsed Drain Current ²	30	A
EAS	Single Pulse Avalanche Energy ³	23	mJ
I_{AS}	Avalanche Current	9	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	40	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	25	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 , (unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =9 A	---	---	34	mΩ
		V _{GS} =4.5V , I _D =7A	---	---	46	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.6	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =28V , V _{GS} =0V , T _J =25℃	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =9A	---	30	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	3.6	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =4.5V , I _D =9 A	---	8.9	---	nC
Q _{gs}	Gate-Source Charge		---	1.5	---	
Q _{gd}	Gate-Drain Charge		---	2.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V , V _{GEN} =10V , R _G =6Ω I _D =1A, R _L =15Ω	---	6	8.8	ns
T _r	Rise Time		---	8.2	14	
T _{d(off)}	Turn-Off Delay Time		---	16	24	
T _f	Fall Time		---	4	8	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	650	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	57	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V , L=0.5mH , I _{AS} =9A	18	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current	---	---	2	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	50	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =2.3A , T _J =25℃	---	---	1.1	V
t _{rr}	Reverse Recovery Time	I _F =9A , di/dt=100A/μs , T _J =25℃	---	6	---	nS
Q _{rr}	Reverse Recovery Charge		---	3.9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, I_{AS}=9A
- 4.The power dissipation is limited by 150℃ junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

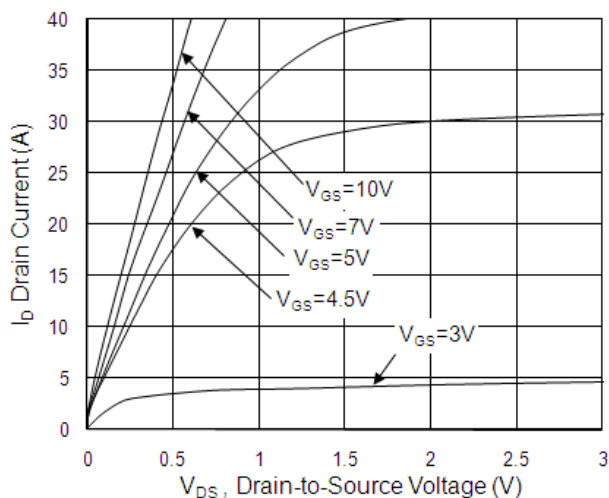


Fig.1 Typical Output Characteristics

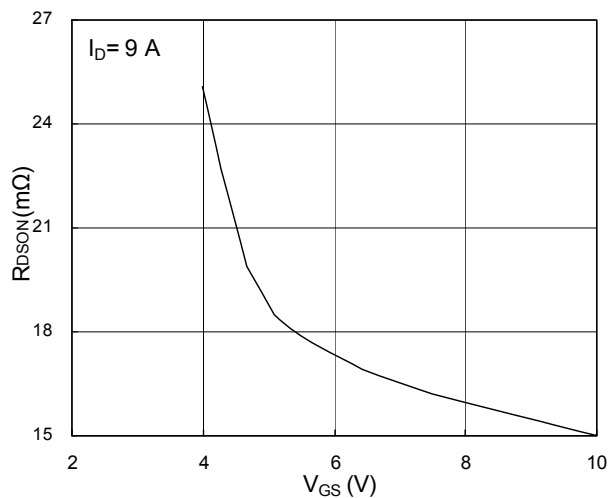


Fig.2 On-Resistance vs. G-S Voltage

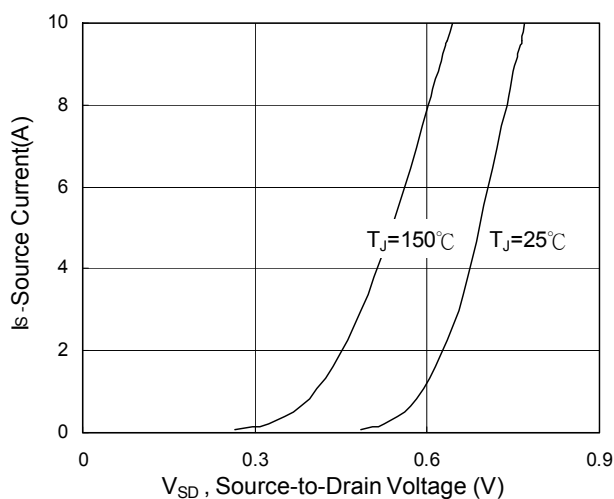


Fig.3 Forward Characteristics Of Reverse

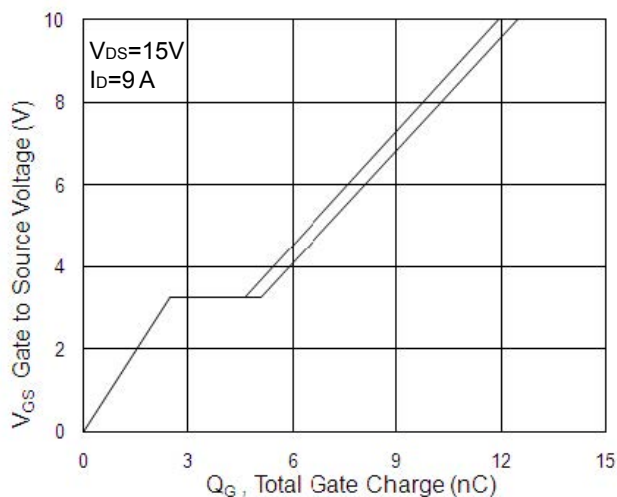
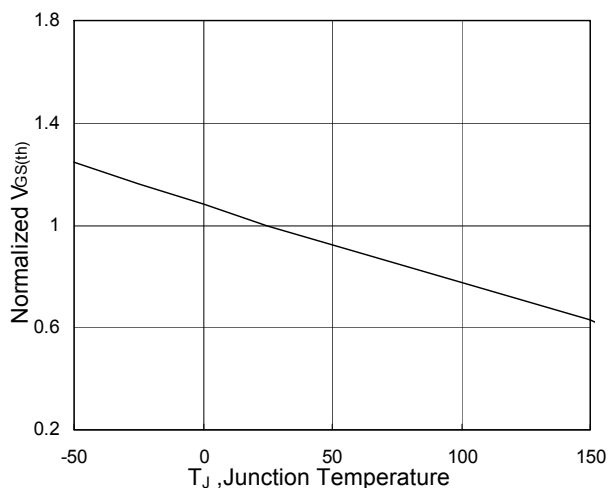


Fig.4 Gate-Charge Characteristics



(°C) Fig.5 Normalized $V_{GS(th)}$ vs. T_J

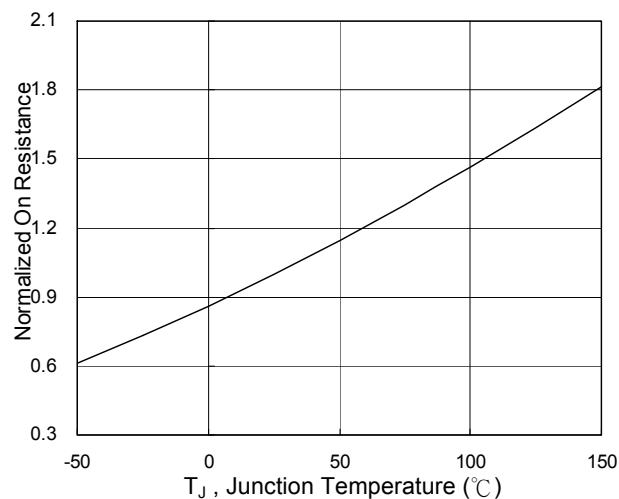


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

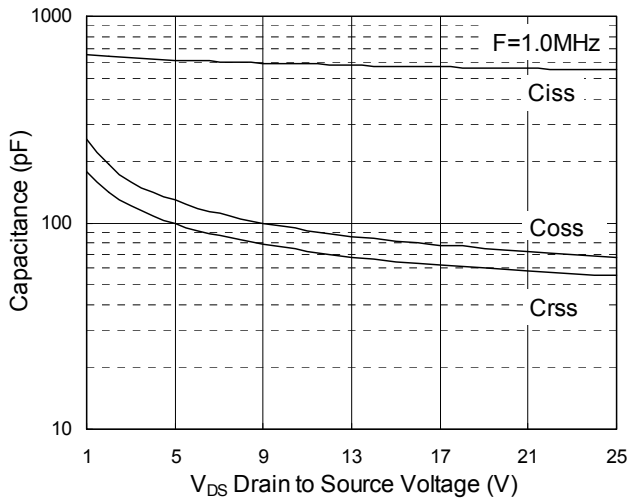


Fig.7 Capacitance

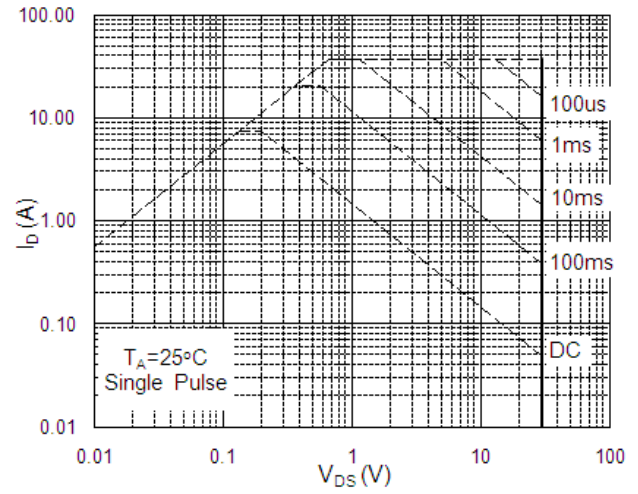


Fig.8 Safe Operating Area

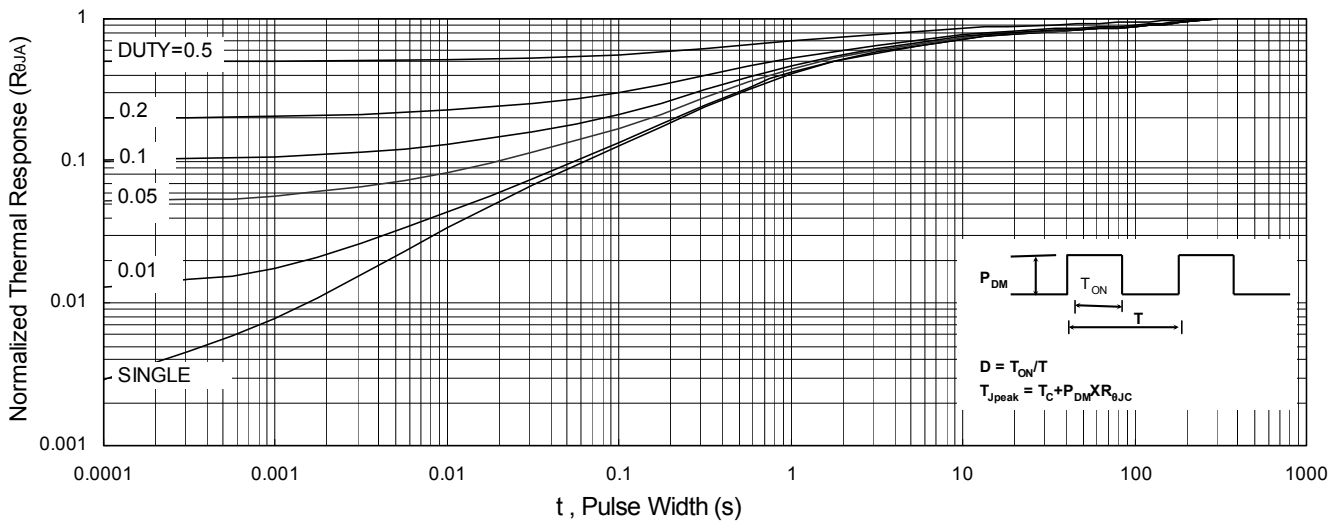


Fig.9 Normalized Maximum Transient Thermal Impedance

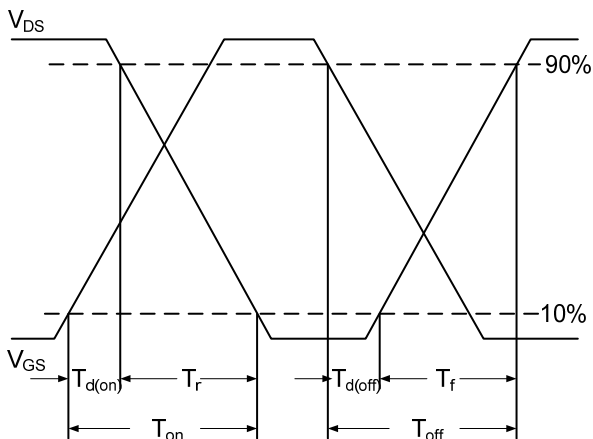


Fig.10 Switching Time Waveform

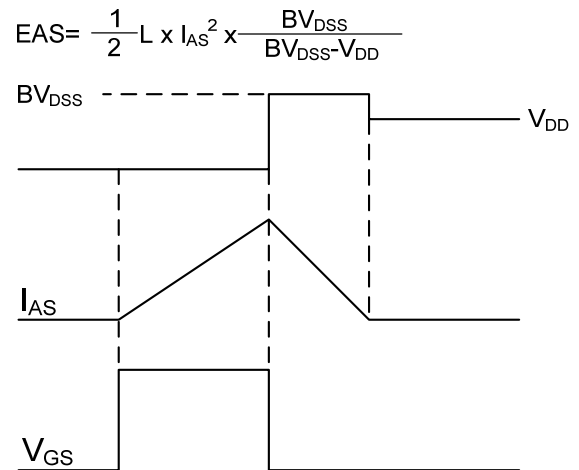
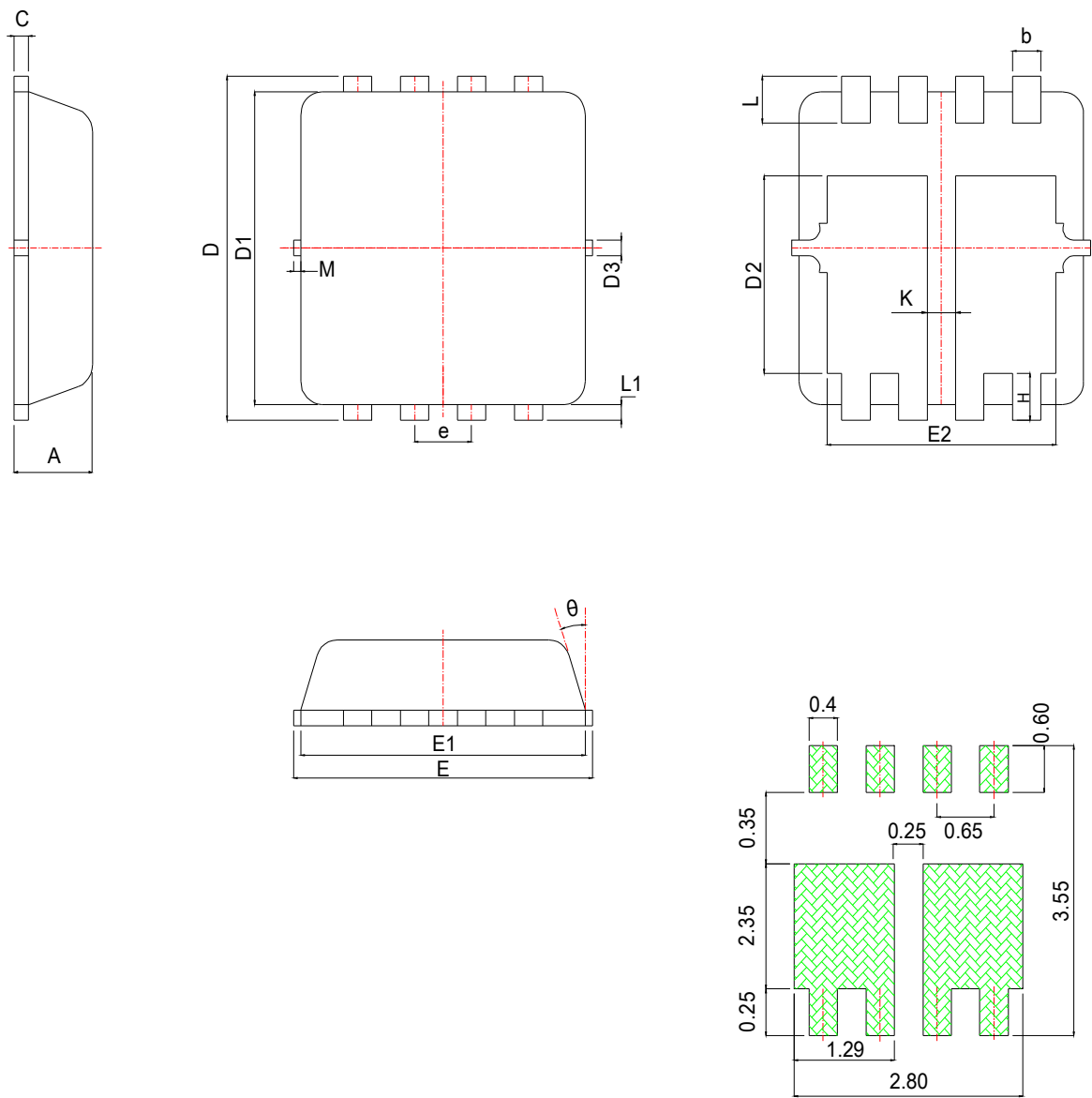


Fig.11 Unclamped Inductive Switching Waveform

PDFN3333



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031	E1	3.00	3.15	3.20	0.118	0.122	0.126
b	0.25	0.30	0.35	0.010	0.012	0.014	E2	2.39	2.49	2.59	0.094	0.098	0.102
c	0.10	0.15	0.25	0.004	0.007	0.010	e	0.65BSC			0.026BSC		
D	3.25	3.35	3.45	0.128	0.132	0.136	H	0.30	0.40	0.50	0.012	0.016	0.020
D1	3.00	3.10	3.20	0.118	0.122	0.126	L	0.30	0.40	0.50	0.012	0.016	0.020
D2	1.78	1.88	1.98	0.070	0.074	0.078	L1	*	0.13	*	*	0.005	*
D3	*	0.13	*	*	0.005	*	θ	*	10°	12°	*	10°	12°
E	3.20	3.30	3.40	0.126	0.130	0.134	M	*	*	0.15	*	*	0.006
K	0.30	*	*	0.012	*	*							